

# AFTER MID

13 MAR 2024

## # Carry Select Adder

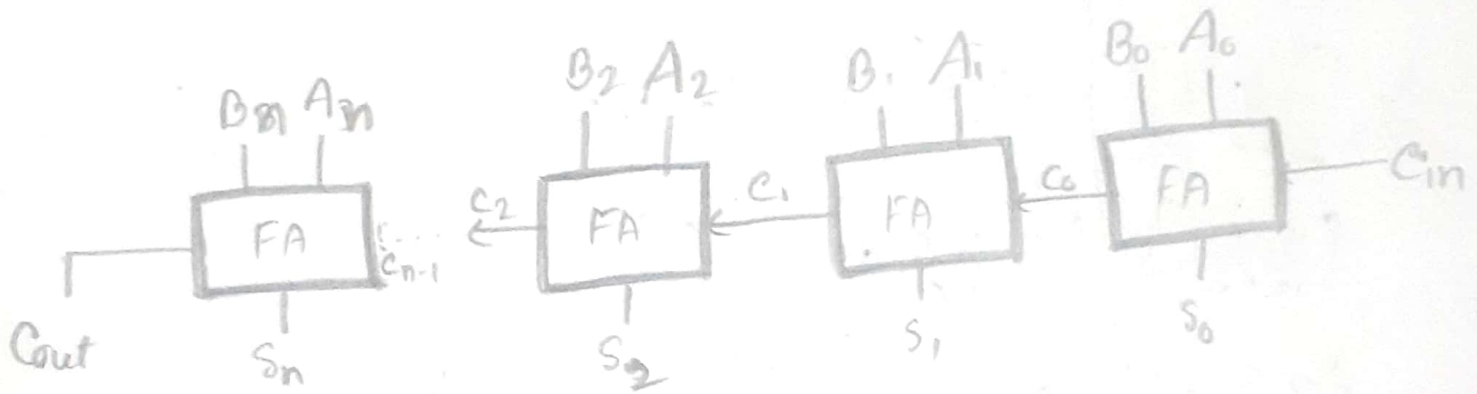


Figure : n bit ripple carry adder.

if we consider a n-bit ripple carry adder and  $k_1$  is the delay for a FA.

Total delay,  $T = \frac{nk_1}{\infty}$  — (1)

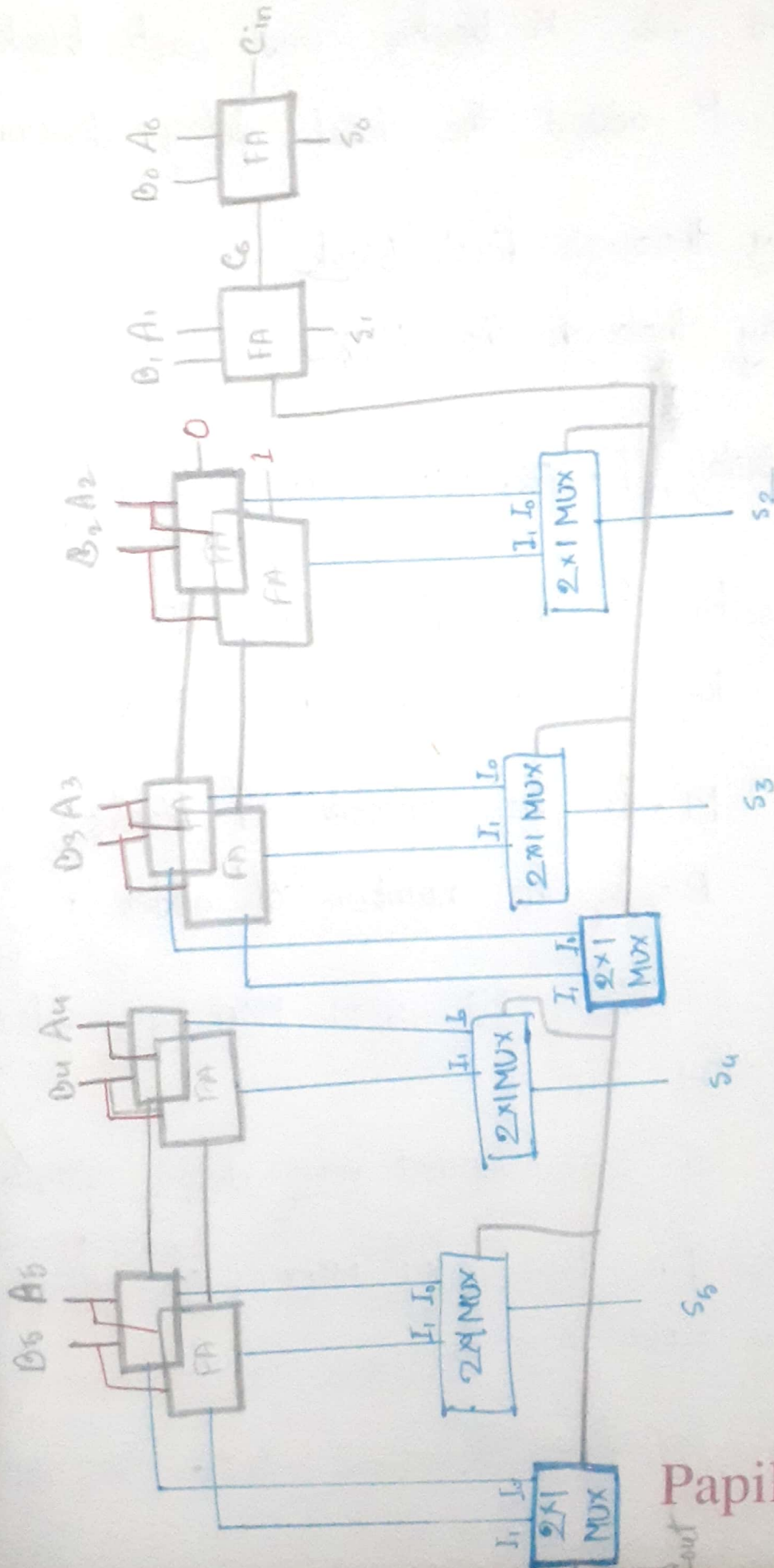
# # 6-bit carry select adder

2bit

2bit connect

into mux connect

2bit



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if we consider a  $n$ -bit carry select adder is divided into  $M$  blocks and each block contains  $P$  added the total delay depends on-

1. Delay through first block
2. Delay through the MUX

so, total Delay,  $T = Pk_1 + (M-1)k_2$  — (2)

where,  $k_1$  = is the delay for FA

$k_2$  = is the delay for MUX

$M$  = is the number of blocks

$P$  = is the number of adder.

□ একটা FA delay ২টা, একটা MUX এর selection এর Delay ২টা।

□ gate এর উপর depend করে delay হবে।

□ একটা FA আর ২x১ MUX এর মধ্যে মোট delay বেশি হবে।

Ans: ৫ gate লাগে।



□ ହାଲି ହାଲି ହାଲି FA delay = 1 sec ଅଟେ

$$k_1 = 1 \text{ sec}, n = 20 \text{ bit}$$

①  $\rightarrow$  total delay,  $T = nk_1 = 20 \times 1 = 20 \text{ delay}$

②  $T = 20 \rightarrow 2 \times pk_1 + (M-1)k_2$

$$= 2 \times 1 + (10-1) \cdot 1$$

$$= 2 + 9 \text{ sec}$$

$$= 11 \text{ sec}$$

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## ≠ Programmable Logic Array (PLA)

AND-OR PLA

$$F_1 = \bar{x}y + xyz + zx = P_1 + P_2 + P_3$$

$$F_2 = xyz + \bar{x}\bar{y}z + \bar{x}zy = P_2 + P_4 + P_5$$

□ 1ଟି PLA 3ଟି input, 2ଟି output, 5ଟି Product

□  $V =$  number of input

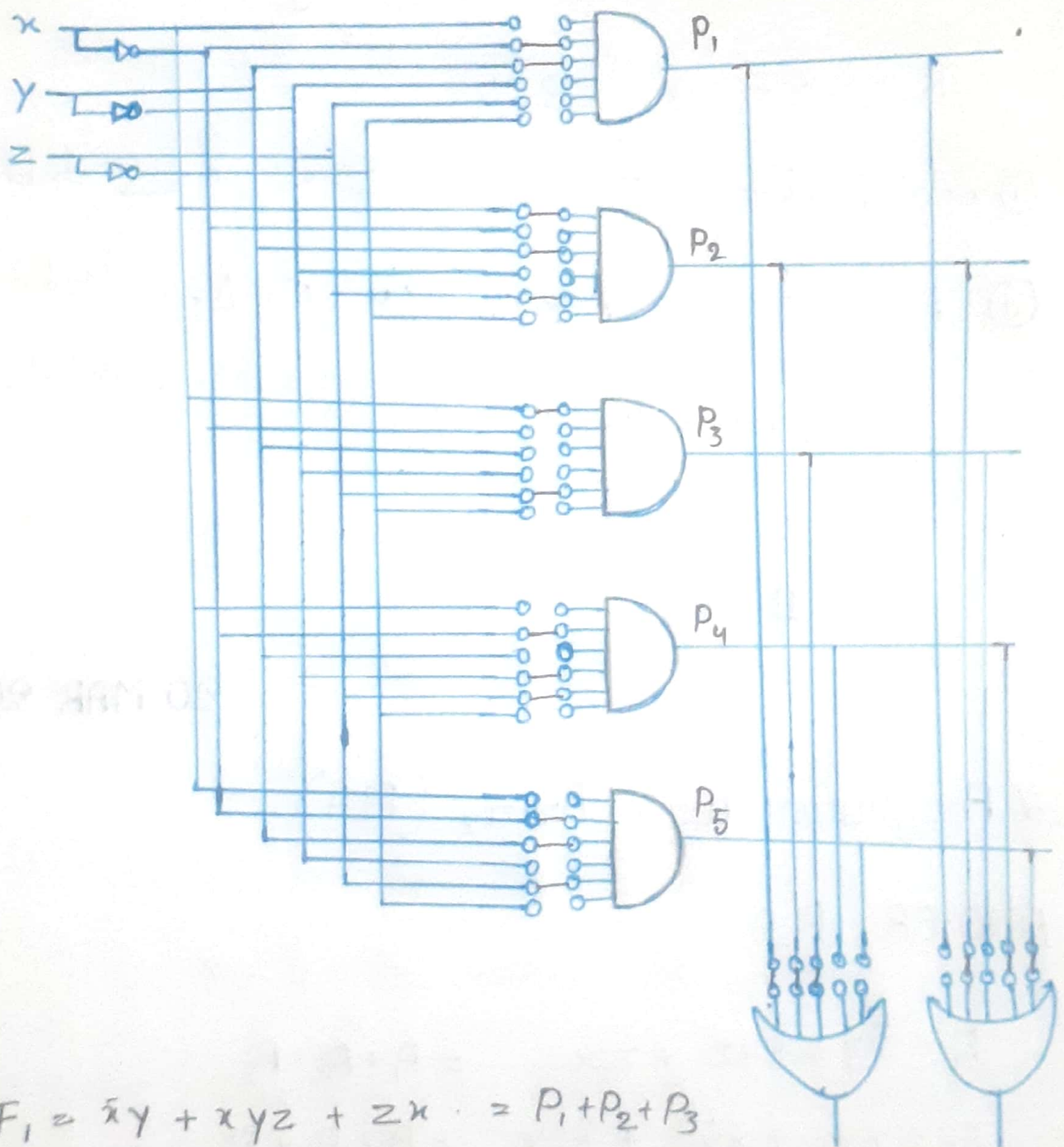
$P =$  number of product

$Z =$  number of output

$$\square \text{ size of PLA} = V \times P \times Z$$

$$= 3 \times 5 \times 2$$

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$$F_1 = \bar{x}y + x\bar{y}z + z\bar{x} = P_1 + P_2 + P_3$$

$$F_2 = xyz + \bar{x}\bar{y}z + \bar{x}zy = P_2 + P_4 + P_5$$

□ NOR gate লগ্নি implement করতে ৬১৫/৭

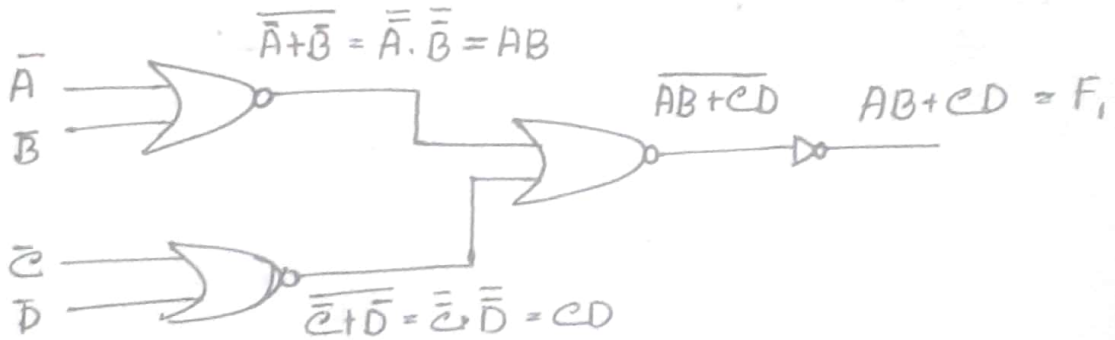
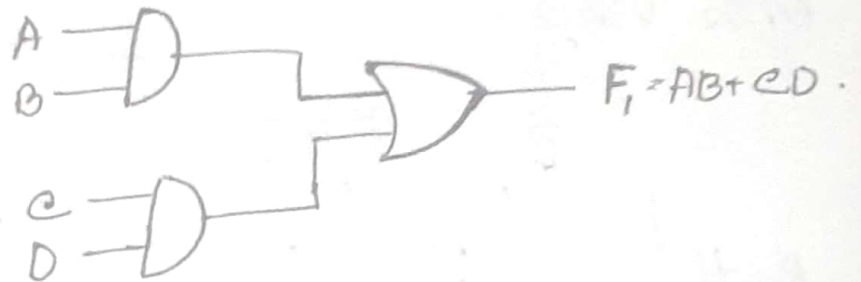
NMOS - ১ input কে inverse করতে হবে,

final output কে আবার inverse/বার/[A] হবে,

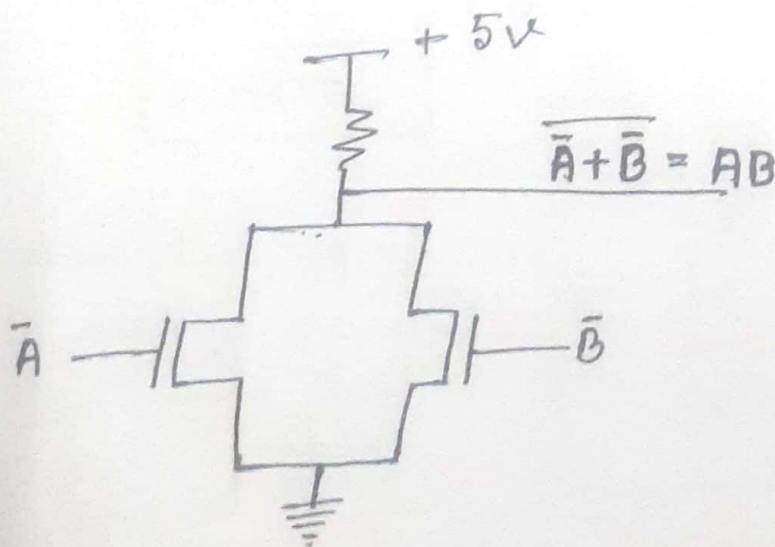
# NOR - NOR

$$F_1 = AB + CD$$

circuit normal



using NOR gate with NMOS





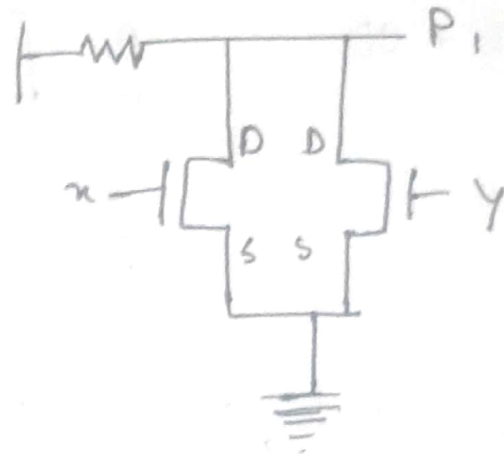
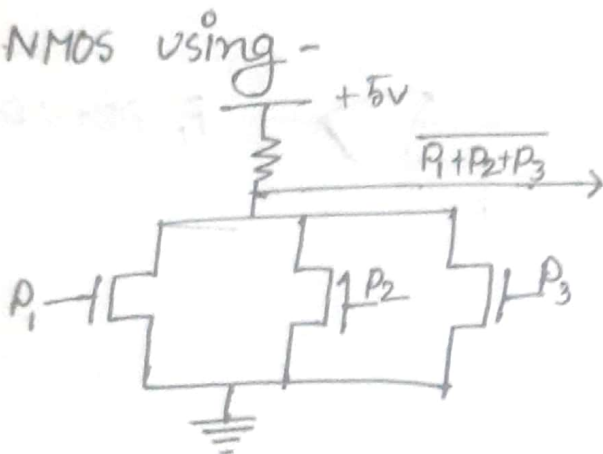
## # NOR - NOR PLA

$$F_1 = \bar{x}\bar{y} + x\bar{y}z + zx = P_1 + P_2 + P_3$$

$$F_2 = x\bar{y}z + \bar{x}y + xy\bar{z} = P_2 + P_4 + P_5$$

size of PLA = (3x5x2)

NMOS using -



# Threshold voltage : threshold voltage is the minimum gate voltage that is needed to create a conducting path between Drain and Source.

□ gate ১৭ ম(রি) ৫ পরিমাণ voltage supply দিলাম

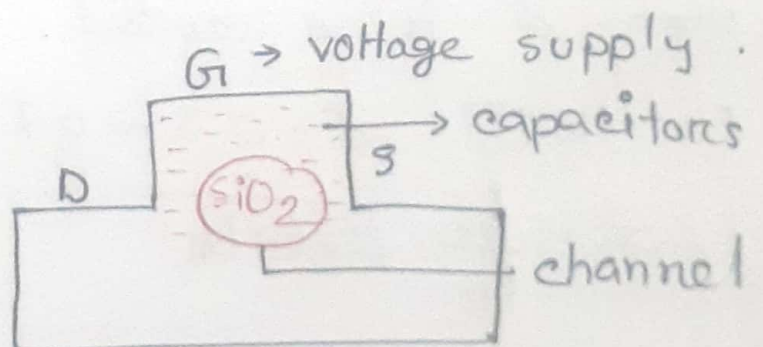
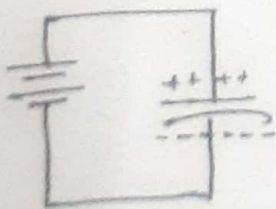
Drain & Source

ম(রি) ৫ পরিমাণ conducting path তৈরি হয় বলে আমরা threshold voltage বলি।

- gate ১ ৫ supply ওই Drain & source ২০ ম(রি) channel তৈরি করে।

+++++	→ metal charge, $Q_g$
oxide	→ oxide charge, $Q_{ss}$
channel	→ inversion channel charge, $Q_c$
⊖⊖⊖	→ Depletion. Region charge, $Q_d$
substrate	

Capacitors,  $C_g$



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we can write,  $Q_g + Q_{ss} = Q_c + Q_d$

$$\therefore Q_g = Q_c + Q_d - Q_{ss}$$

$$\text{Threshold voltage, } V_t = \frac{Q_g}{C_g} = \frac{Q_c + Q_d - Q_{ss}}{C_g}$$

where,  $C_g$  is the gate capacitance

### # Body effect

a body terminal source or drain side

short / not connected to ground voltage is zero

if body is not connected to ground, this is called Body effect.

if we consider  $V_{t0}$  is the threshold voltage

when,  $V_{sb} = 0$

$$\text{if } V_{sb} \neq 0, \text{ then } V_t = V_{t0} + \gamma \sqrt{V_{sb}}$$

where  $\gamma$  is a constant.

For MOSFET,  $\gamma = 0.3 \sim 0.7$

$$\gamma = \frac{t_{ox}}{C_{ox}} \sqrt{2q\epsilon_{si} N_A}$$

where,  $t_{ox}$  = thickness of  $O_2$

$\epsilon_{ox}$  = Oxide Permittivity

$q$  = charge of an electron

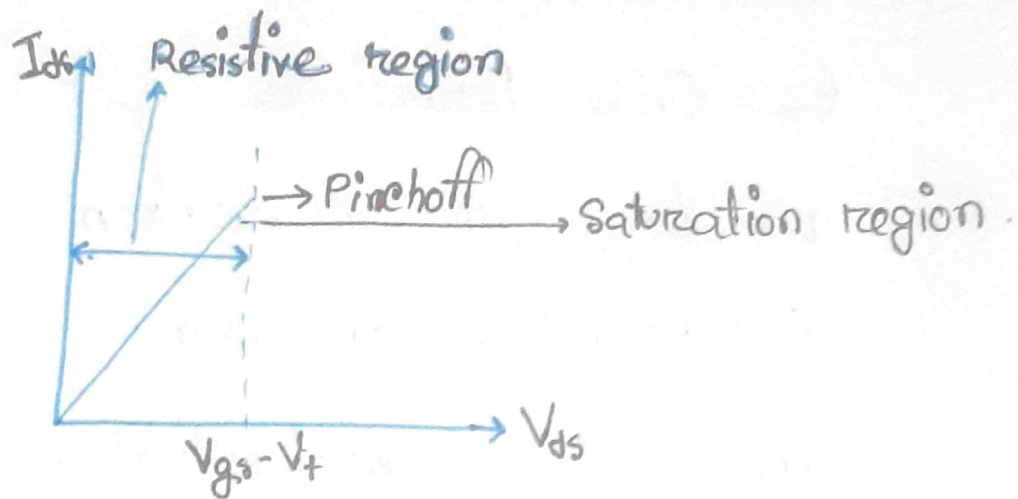
$\epsilon_s$  = Permittivity of silicon

$N_A$  = Doping Concentration

$V_{SB} = 0$  24 threshold (4/4) (4/4) 6/4 equation 4/4

$V_{GB} \neq 0$  হলে গাটল ব্য়ব body effect আছে,  
তখন গাটল equation বসাবে.

# # I-V characteristics of MOSFET



- MOSFET bi mode (Resistive / Saturation region)
- bi mode (NMOS / PMOS) calculated as follows

for NMOS

if  $V_{DS} < V_{GS} - V_t$

resistive mode

$$I_{DS} = \frac{\epsilon M_n}{D} \cdot \frac{W_n}{L_n} \left\{ (V_{GS} - V_t) V_{DS} - \frac{V_{DS}^2}{2} \right\}$$

if  $V_{DS} \geq V_{GS} - V_t$

saturation mode

$$I_{DS} = \frac{\epsilon M_n}{2D} \cdot \frac{W_n}{L_n} \left\{ (V_{GS} - V_t)^2 \right\}$$



## For PMOS

### resistive Mode

$$\text{if } V_{sd} < V_{sg} - V_t$$

$$I_{sd} = \frac{\epsilon M_p}{D} \cdot \frac{W_p}{L_p} \left\{ (V_{sg} - V_t) V_{sd} - \frac{V_{sd}^2}{2} \right\}$$

### saturation Mode

$$\text{if } V_{sd} \geq V_{sg} - V_t$$

$$I_{sd} = \frac{\epsilon M_p}{2D} \cdot \frac{W_p}{L_p} (V_{sg} - V_t)^2$$

Where,  $D \rightarrow$  Depth of  $O_2$

$M_n \rightarrow$  Mobility of Electron

$M_p \rightarrow$  Mobility of Hole

$\epsilon \rightarrow$  Permittivity

$W_p/W_n \rightarrow$  channel width

$L_p/L_n \rightarrow$  channel length

$$V_{gs} = V_g - V_s$$

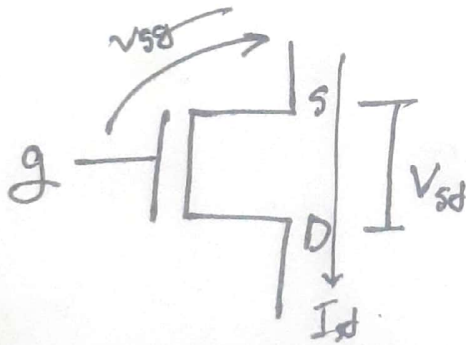
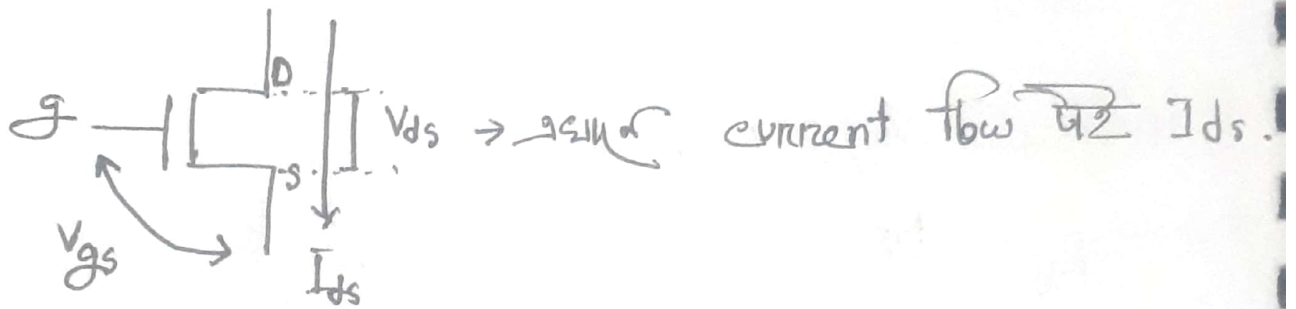
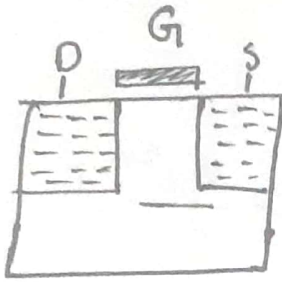
$V_g =$  gate voltage

$V_s =$  source voltage

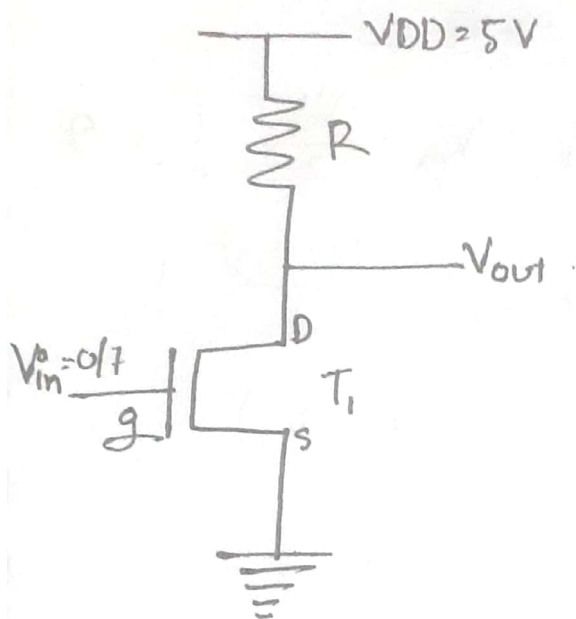
pinchoff = point at which voltage across  $I_{ds}$  is zero

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MOSFET - 2006 electronic switch.



# ± NMOS inverter with Resistive load



let,  $\mu_n = 30 \text{ MA/V}^2$

$$\frac{W}{L} = 1$$

$$V_t = 1 \text{ V}$$

Solve - if  $V_{in} = 0$ ,  $T_1 \rightarrow \text{OFF}$ ,  $T_2 \rightarrow \text{Always on}$ .

$$V_{out} = V_{DD} - V_R = V_{DD} - V_{t2}$$

□ (OFF transistor not need,

CZ,  $V_{in} = 0$  2nd current flow 2nd transistor.]

if  $V_{in} = 5 \text{ V}$ ,  $T_1 \rightarrow \text{ON}$ .

$$V_{out} = \frac{1}{3} \times V_t = 0.33 \text{ V}$$

$$V_{ds} = V_d - V_s = \overset{\text{Vout} \rightarrow}{0.33} - \overset{\text{gnd} \rightarrow \text{connect}}{0} = 0.33 \text{ V}$$

$$\overset{\text{vin supply 2nd } 5 \text{ V}}{V_{gs}} = V_g - V_s = 5 - 0 = 5 \text{ V}$$

$$\text{now, } V_{gs} - V_t = 5 - 1 = 4 \text{ V}$$



$$\text{see, } V_{ds} < V_{gs} - V_t; \quad 0.33\text{V} < 4\text{V}$$

$T_1$  operates at resistive mode.

$$T_1 = I_{ds} = \frac{\mu_n}{D} \cdot \frac{W_n}{L_n} \left\{ (V_{gs} - V_t) V_{ds} - \frac{V_{ds}^2}{2} \right\} = ?$$

here,

$$\frac{\mu_n}{D} = 30 \text{ MA/V}^2$$

$$\frac{W_n}{L_n} = 1.$$

$$V_{gs} = 4\text{V}$$

$$V_t = 1\text{V}$$

$$V_{ds} = 0.33$$

$$= 30 \times 1 \left\{ (4-1) \times 0.33 - \frac{(0.33)^2}{2} \right\}$$

$$= 30 (4 \times 0.33 - 0.05445)$$

$$= 30 \times 0.26555$$

$$= 37.96 \text{ MA}$$

$$R = \frac{V_{DD} - V_{out}}{I_{ds}}$$

$$= \frac{5 - 0.33}{37.96 \times 10^{-6}}$$

$$= 123056.65 \, \Omega$$

$$= 123 \text{ k}\Omega.$$

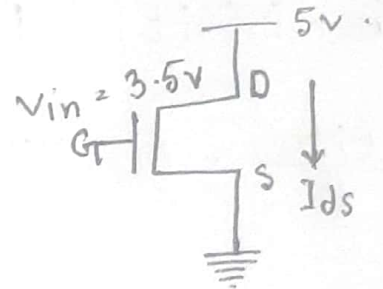
Ans

Example :  $V_{DD} = 3V$ ,  $\frac{\mu_n}{D} = 50 \text{ mA/V}^2$ ,  $\frac{W}{L} = 4$

$R = ?$   $V_t = 0.75V$ ,  $V_{ds} = 0.2V$ ,  $V_{in} = 3.5V$

Solve : If  $V_{in} = 0$ ,  $I_{ds} = \text{OFF}$

If  $V_{in} = 5V$ ,  $I_{ds} = \text{ON}$



$$V_{in} = 3.5V = V_g$$

$$V_{gs} = V_g - V_s = 3.5 - 0V = 3.5V$$

$$\therefore V_{gs} - V_t = (3.5 - 0.75)V = 2.75V$$

$$\text{see, } V_{ds} < V_{gs} - V_t ; \quad 0.2V < 2.75V$$

$I_{ds}$  operates at resistive Mode.

$$I_{ds} = \frac{\mu_n}{D} \cdot \frac{W}{L} \left\{ (V_{gs} - V_t) V_{ds} - \frac{V_{ds}^2}{2} \right\}$$

$$= 50 \times 4 \left\{ (3.5 - 0.75) 0.2 - \frac{(0.2)^2}{2} \right\}$$

$$= 200 (2.75 \times 0.2 - 0.02)$$

$$= 200 \times 0.53$$

$$= 106$$

A

Problem: A NMOS inverter with Enhancement type load is biased at  $V_{DD} = 3V$ ,

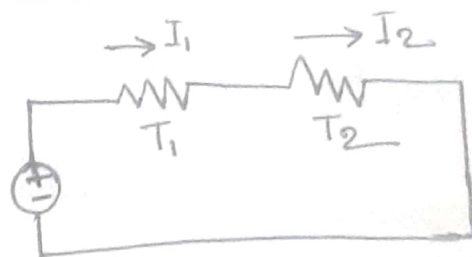
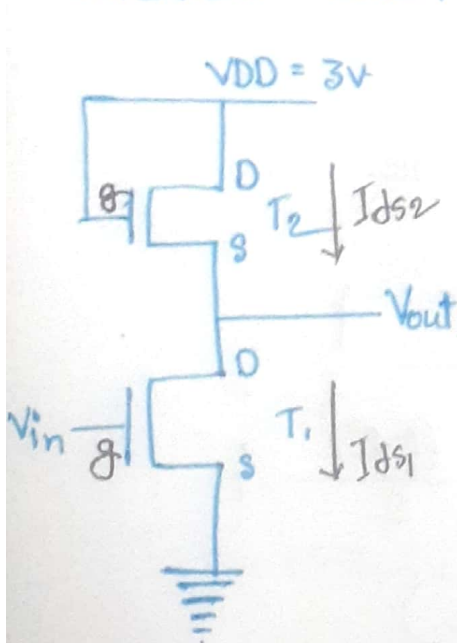
The MOSFET Parameters are  $V_{t1} = V_{t2} = 0.4V$ ,

$$\frac{\mu_n}{D} = 60 \text{ MA/V}^2, \quad \frac{W_1}{L_1} = 16, \quad \frac{W_2}{L_2} = 2$$

Find the output voltage when ①  $V_{in} = 0V$ ,

②  $V_{in} = 2.6V$

Also calculate the Power dissipated in the inverter when  $V_{in} = 2.6V$ .



□ input, output voltage (এক)

একটি একই connection

কোনো কোন mode আছে

আগে জানা নাগবে / এক একা নাগবে

Solve = ①  $V_{in} = 0V$  ২(ম),  $V_{out} = V_{DD} - V_{t2}$   
 $T_1 = \text{off}$   
 $T_2 = \text{always on}$   
 $= 3 - 0.4 = 2.6V$

②  $V_{in} = 2.6V$  ২(ম),  $V_{ds} = V_d - V_s = V_{out} - V_s$   
 $V_{out} = V_{ds}$   
 $\Rightarrow V_{ds} = V_{out} - 0$



Power dissipated -

T<sub>1</sub>

$$V_{ds} = ?$$

$$V_{gs} = 2.6 \text{ V}$$

$$V_{t1} = 0.4 \text{ V}$$

$$V_{gs} - V_{t1} = 2.2 \text{ V}$$

$$V_{ds} < V_{gs} - V_{t1} ; V_{ds} < V_{gs} - V_{t2}$$

$$\Rightarrow < 2.2$$

$$\Rightarrow 3 < \cancel{3} \cdot 2.6$$

$$\Rightarrow 3 > 2.6$$

saturation Mode.

resistive mode, T<sub>1</sub>.

T<sub>2</sub>

$$V_{ds} = \cancel{V_{DD}} = \cancel{V_{gs}} ?$$

$$V_{gs} = V_{DD} - V_{out}$$

$$= 3 - V_{out}$$

$$V_{t2} = 0.4 \text{ V}$$

$$V_{gs} - V_{t2} = 3 - 0.4 = 2.6$$

now,  $I_{ds1} = I_{ds2}$  input  $\rightarrow$  output  $V_{out} = V_{ds}$

$$\Rightarrow \frac{\epsilon_{Mn}}{D} \cdot \frac{W_1}{L_1} \left\{ (\underline{V_{gs}} - \underline{V_{t1}}) V_{ds} - \frac{V_{ds}^2}{2} \right\}$$

$$= \frac{\epsilon_{Mn}}{2D} \cdot \frac{W_2}{L_2} \cdot (\underline{V_{gs}} - \underline{V_{t2}})^2$$

$$\Rightarrow 16 \left\{ (\underline{2.6} - \underline{0.4}) V_{ds} - \frac{V_{ds}^2}{2} \right\} = \frac{1}{2} \cdot 2 \left( \underline{3} - \frac{V_{out}}{V_{ds}} - \underline{0.4} \right)^2$$

$$\Rightarrow 16 \times \left\{ \underline{2.2} V_{ds} - \frac{V_{ds}^2}{2} \right\} = (V_{ds} - \underline{2.6})^2$$

$$\Rightarrow 16 \times \left( \frac{4.4 V_{ds} - V_{ds}^2}{2} \right) = V_{ds}^2 - 5.2 V_{ds} + 6.76$$

$$\Rightarrow 8 (4.4 V_{ds} - V_{ds}^2) = V_{ds}^2 - 5.2 V_{ds} + 6.76$$

$$\Rightarrow 35.2 V_{ds} - 8 V_{ds}^2 - V_{ds}^2 + 5.2 V_{ds} - 6.76 = 0$$

$$\Rightarrow -9 V_{ds}^2 + 40.4 V_{ds} - 6.76 = 0$$

$$\Rightarrow V_{ds}^2 - 4.489 V_{ds} + 0.75 = 0$$

$$\Rightarrow V_{ds}^2 - 2 \times 2.2445 \times V_{ds} + (2.2445)^2 - 4.288 = 0$$

$$\Rightarrow (V_{ds} - 2.2445)^2 - 4.288 = 0$$

$$\Rightarrow \sqrt{(V_{ds} - 2.2445)^2} = \sqrt{4.288}$$

$$\Rightarrow V_{ds} = 2.07 + 2.2445$$

$$\therefore V_{ds} = 4.315 \text{ V}$$

$$\begin{aligned}
 I_{ds2} &= \frac{\mu_n}{2L} \cdot \frac{W_2}{L_2} (V_{gs} - V_{t2})^2 \\
 &= \frac{60}{2} \times 2 (3 - 0.174 - 0.4)^2 \\
 &= 353 \text{ MA}
 \end{aligned}$$

$$\therefore P = VI$$

$$= 3 \times I_{ds}$$

$$= 3 \times 353 \times 10^{-6} \cdot N$$

$$= 0.001059 \text{ N.}$$

*[Signature]*



Problem:  $V_{DD} = 5V$ ,  $V_{t1} = V_{t2} = 0.8V$ .

$\frac{I_{Mn}}{D}$ ,  $35 \text{ MA/V}^2$ ,  $V_0 = 0.1V$ ,  $V_{in} = 4.2V$ .

$$\frac{W_1/L_1}{W_2/L_2} = ?$$

$$P = ?$$

Solve: if  $V_0 = 0V$ ,  $T_1 = \text{off}$ ,  $T_2 \rightarrow \text{always on}$

$$V_{out} = V_{DD} - V_{t2}$$

$$V_{t0} = 1V$$

$$\gamma = 0.5$$

$$= V_{DD} - (V_{t0} + \gamma \sqrt{V_{SD}})$$

$$\rightarrow V_{out} = 5 - (1 + 0.5 \sqrt{V_{out}})$$

$$\rightarrow V_{out} = 4 - 0.5 \sqrt{V_{out}}$$

$$\rightarrow 2V_{out} = 8 - 0.5 \times 2 \sqrt{V_{out}}$$

$$\rightarrow 2V_{out} = 8 - 1 \sqrt{V_{out}}$$

$$\rightarrow \sqrt{V_{out}} = 8 - 2V_{out}$$

$$\rightarrow V_{out} = 64 - 32V_{out} + 4V_{out}^2$$

$$\rightarrow 4V_{out}^2 - 33V_{out} + 64 = 0$$

$$\rightarrow V_{out}^2 - 8.25V_{out} + 16 = 0$$

$$\rightarrow V_{out}^2 - 2 \times V_{out} \times 4.125 + (4.125)^2 - 1.015625 = 0$$

$$\rightarrow (V_{out} - 4.125)^2 = 1.015625$$

$$\rightarrow V_{out} = 1.015625 + 4.125$$

$$\rightarrow V_{out} = 5.140625$$

$$\therefore V_{out} = 5.13V \text{ or } 3.12V$$